2SA1806

Silicon PNP epitaxial planar type

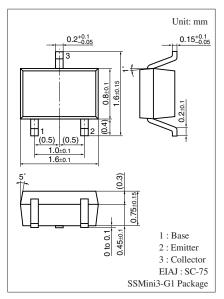
For high speed switching

■ Features

- High speed switching
- Low collector-emitter saturation voltage V_{CE(sat)}
- SS-Mini type package allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-15	V	
Collector-emitter voltage (Base open)	V _{CEO}	-15	V	
Emitter-base voltage (Collector open)	V_{EBO}	-4	V	
Collector current	I_C	-50	mA	
Peak collector current	I_{CP}	-100	mA	
Collector power dissipation	P _C	125	mW	
Junction temperature	T_j	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C	



Marking Symbol: AK

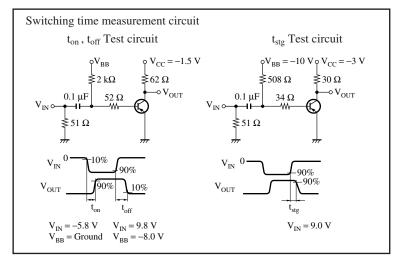
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

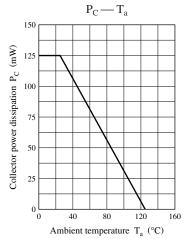
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -8 \text{ V}, I_{E} = 0$			- 0.1	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{CE} = -3 \text{ V}, I_{C} = 0$			- 0.1	μΑ
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -1 \text{ V}, \ I_{C} = -10 \text{ mA}$	50		150	_
	h _{FE2}	$V_{CE} = -1 \text{ V}, I_{C} = -1 \text{ mA}$	30			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$		- 0.1	- 0.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$	800	1500		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -5 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1		pF
(Common base, input open circuited)						
Turn-on time	t _{on}	Refer to the switching time measurement circuit		12		ns
Turn-off time	t _{off}			20		ns
Storage time	t _{stg}			19		ns

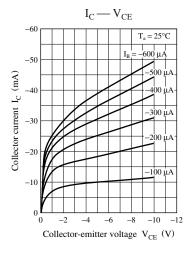
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

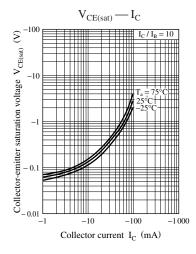
2. *: Rank classification

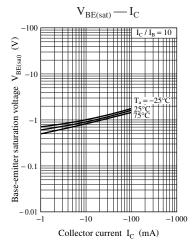
Rank	Q	R
h _{FE1}	50 to 120	90 to 150

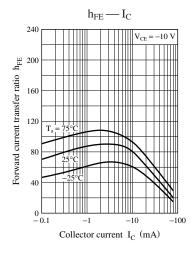


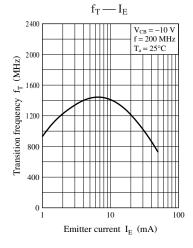


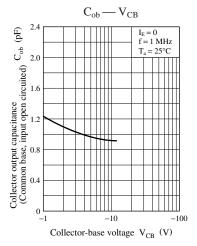












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